

MOSFET – SiC Power, Single N-Channel, D2PAK-7L

1200 V, 160 mΩ, 19.5 A



ON Semiconductor®

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NVBG160N120SC1

Features

- Typ. $R_{DS(on)} = 160\text{ m}\Omega$
- Ultra Low Gate Charge (typ. $Q_{G(tot)} = 33.8\text{ nC}$)
- Low Effective Output Capacitance (typ. $C_{oss} = 50.7\text{ pF}$)
- 100% Avalanche Tested
- Qualified According to AEC-Q101
- This Device is Pb-Free and is RoHS Compliant

Typical Applications

- Automotive On Board Charger
- Automotive DC/DC converter for EV/HEV

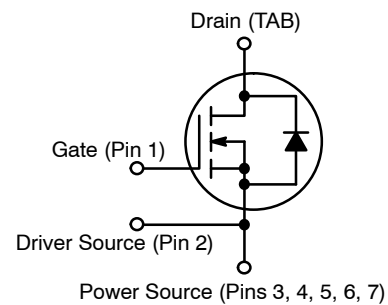
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DSS}	1200	V
Gate-to-Source Voltage		V_{GS}	-15/+25	V
Recommended Operation Values of Gate – Source Voltage		$T_C < 175^\circ\text{C}$ V_{GSop}	-5/+20	V
Continuous Drain Current (Note 1)	Steady State $T_C = 25^\circ\text{C}$	I_D	19.5	A
Power Dissipation (Note 1)		P_D	136	W
Continuous Drain Current (Note 1)	Steady State $T_C = 100^\circ\text{C}$	I_D	13.7	A
Power Dissipation (Note 1)		P_D	68	W
Pulsed Drain Current (Note 2)		$T_A = 25^\circ\text{C}$ I_{DM}	78	A
Single Pulse Surge Drain Current Capability	$T_A = 25^\circ\text{C}$, $t_p = 10\text{ }\mu\text{s}$, $R_G = 4.7\text{ }\Omega$	I_{DSC}	140	A
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +175	$^\circ\text{C}$
Source Current (Body Diode)		I_S	13.6	A
Single Pulse Drain-to-Source Avalanche Energy ($I_L = 15.5\text{ A}_{pk}$, $L = 1\text{ mH}$) (Note 3)		E_{AS}	120	mJ
Maximum Lead Temperature for Soldering, 1/8" from Case for 10 Seconds		T_L	300	$^\circ\text{C}$

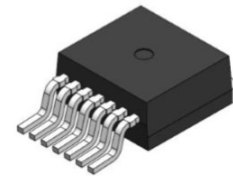
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Repetitive rating, limited by max junction temperature.
3. E_{AS} of 120 mJ is based on starting $T_J = 25^\circ\text{C}$; $L = 1\text{ mH}$, $I_{AS} = 15.5\text{ A}$, $V_{DD} = 120\text{ V}$, $V_{GS} = 18\text{ V}$.

$V_{(BR)DSS}$	$R_{DS(ON)}\text{ MAX}$	$I_D\text{ MAX}$
1200 V	224 mΩ @ 20 V	19.5 A

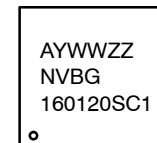


N-CHANNEL MOSFET



D2PAK-7L
CASE 418BJ

MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- WW = Work Week
- ZZ = Lot Traceability
- NVBG160120SC1 = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

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Table 1. THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Units
Thermal Resistance Junction-to-Case (Note 1)	$R_{\theta JC}$	1.1	$^{\circ}C/W$
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	40	$^{\circ}C/W$

Table 2. ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0 V, I_D = 1 mA$	1200			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 1 mA$, refer to $25^{\circ}C$		0.7		$V/^{\circ}C$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0 V$ $V_{DS} = 1200 V$	$T_J = 25^{\circ}C$		100	μA
			$T_J = 175^{\circ}C$		1	mA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = +25/-15 V, V_{DS} = 0 V$			± 1	μA
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 2.5 mA$	1.8	3	4.3	V
Recommended Gate Voltage	V_{GOP}		-5		+20	V
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 20 V, I_D = 12 A, T_J = 25^{\circ}C$		160	224	m Ω
		$V_{GS} = 20 V, I_D = 12 A, T_J = 175^{\circ}C$		239	365	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 10 V, I_D = 12 A$		5.5		S
CHARGES, CAPACITANCES & GATE RESISTANCE						
Input Capacitance	C_{ISS}	$V_{GS} = 0 V, f = 1 MHz,$ $V_{DS} = 800 V$		678		pF
Output Capacitance	C_{OSS}			50.7		
Reverse Transfer Capacitance	C_{RSS}			5.87		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -5/20 V, V_{DS} = 600 V,$ $I_D = 16 A$		33.8		nC
Threshold Gate Charge	$Q_{G(TH)}$			6.1		
Gate-to-Source Charge	Q_{GS}			11.6		
Gate-to-Drain Charge	Q_{GD}			9.6		
Gate-Resistance	R_G	$f = 1 MHz$		1.39		Ω
SWITCHING CHARACTERISTICS (Note 4)						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -5/20 V, V_{DS} = 800 V,$ $I_D = 16 A, R_G = 6 \Omega,$ Inductive Load		11	20	ns
Rise Time	t_r			11	20	
Turn-Off Delay Time	$t_{d(OFF)}$			15	27	
Fall Time	t_f			7.4	15	
Turn-On Switching Loss	E_{ON}			120		μJ
Turn-Off Switching Loss	E_{OFF}			28		
Total Switching Loss	E_{TOT}			148		
DRAIN-SOURCE DIODE CHARACTERISTICS						
Continuous Drain-Source Diode Forward Current	I_{SD}	$V_{GS} = -5 V, T_J = 25^{\circ}C$			13.6	A
Pulsed Drain-Source Diode Forward Current (Note 2)	I_{SDM}	$V_{GS} = -5 V, T_J = 25^{\circ}C$			78	A
Forward Diode Voltage	V_{SD}	$V_{GS} = -5 V, I_{SD} = 6 A, T_J = 25^{\circ}C$		3.9		V

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Table 2. ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS						
Reverse Recovery Time	t_{RR}	$V_{GS} = -5/20\text{ V}$, $I_{SD} = 16\text{ A}$, $dI_S/dt = 1000\text{ A}/\mu\text{s}$		15		ns
Reverse Recovery Charge	Q_{RR}			47		nC
Reverse Recovery Energy	E_{REC}			3.9		μJ
Peak Reverse Recovery Current	I_{RRM}			6.6		A
Charge time	T_a			7.0		ns
Discharge time	T_b			7.4		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Switching characteristics are independent of operating junction temperature

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TYPICAL CHARACTERISTICS

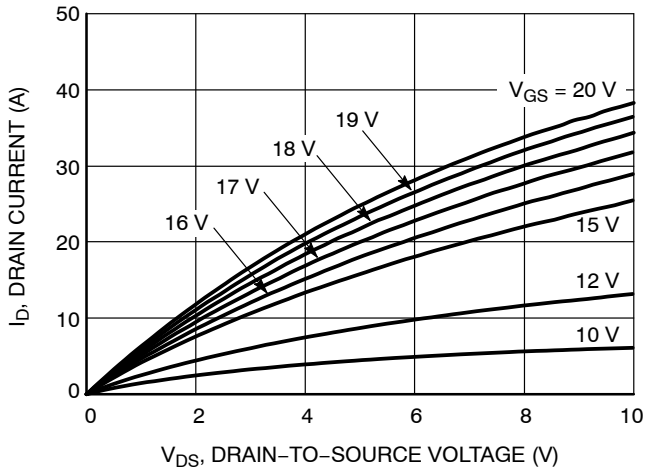


Figure 1. On-Region Characteristics

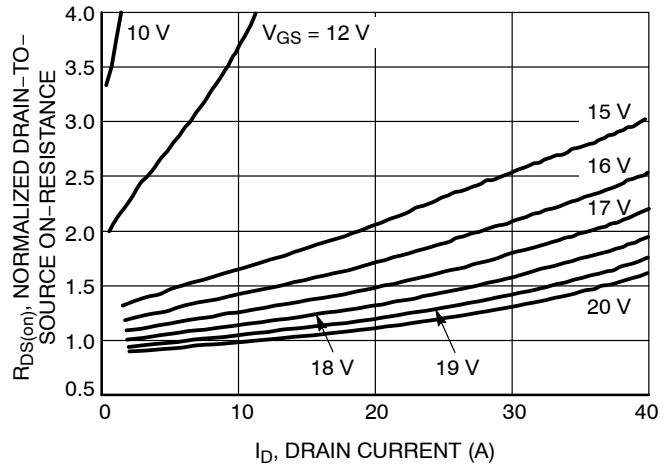


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

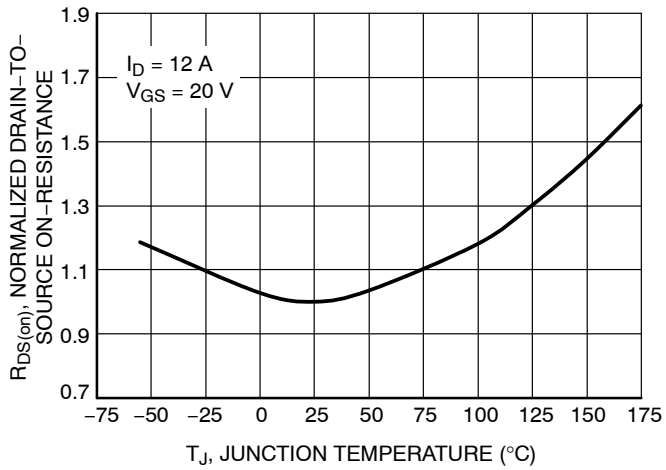


Figure 3. On-Resistance Variation with Temperature

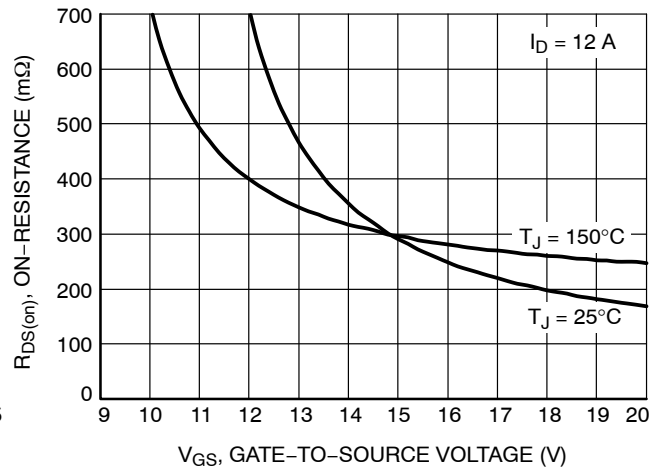


Figure 4. On-Resistance vs. Gate-to-Source Voltage

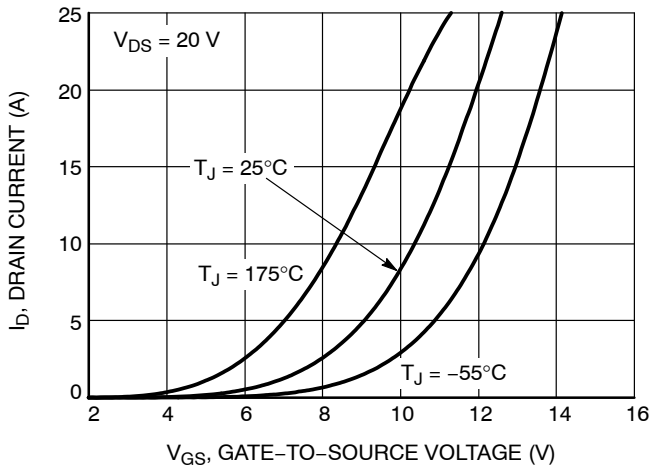


Figure 5. Transfer Characteristics

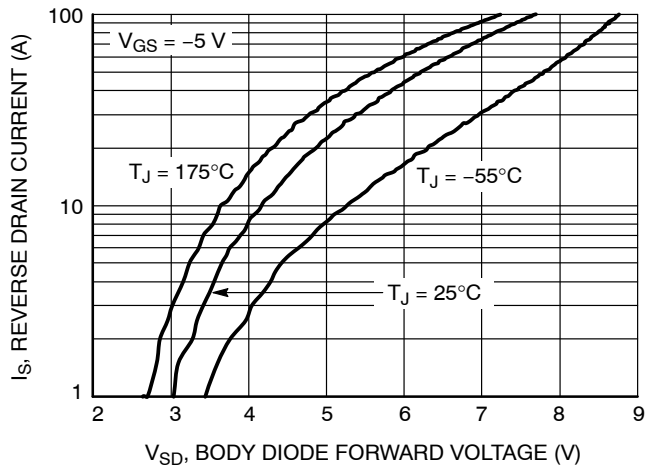


Figure 6. Diode Forward Voltage vs. Current

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TYPICAL CHARACTERISTICS

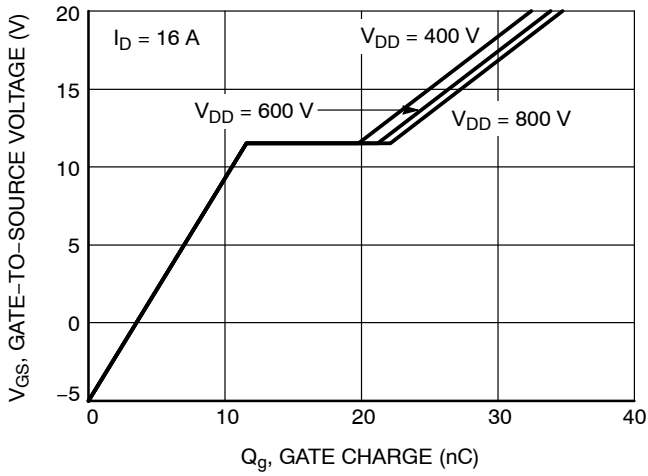


Figure 7. Gate-to-Source Voltage vs. Total Charge

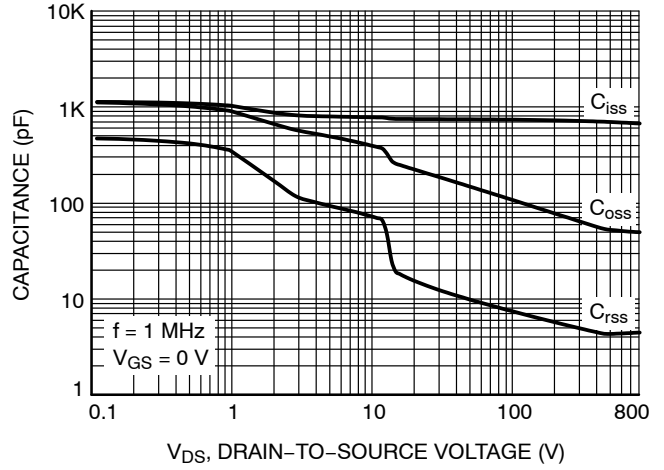


Figure 8. Capacitance vs. Drain-to-Source Voltage

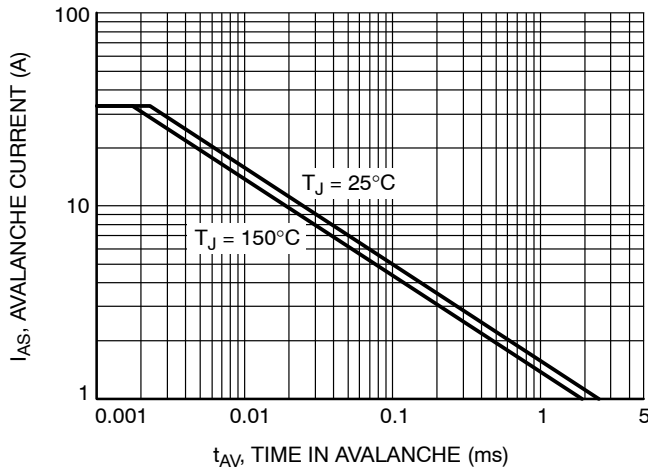


Figure 9. Unclamped Inductive Switching Capability

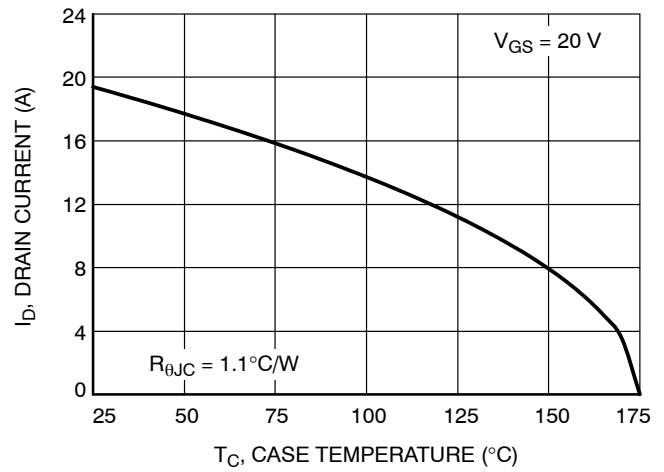


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

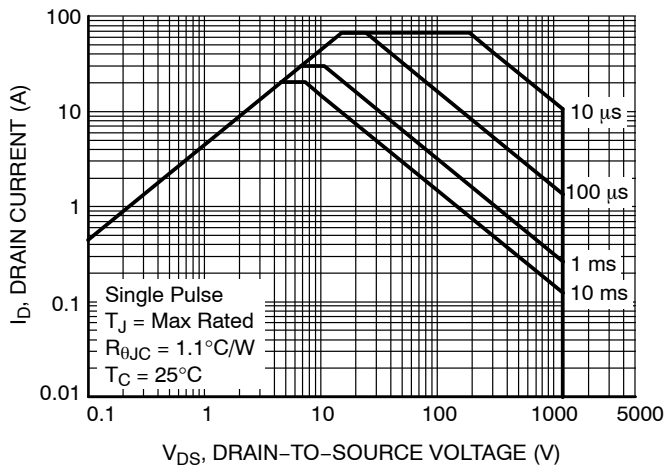


Figure 11. Safe Operating Area

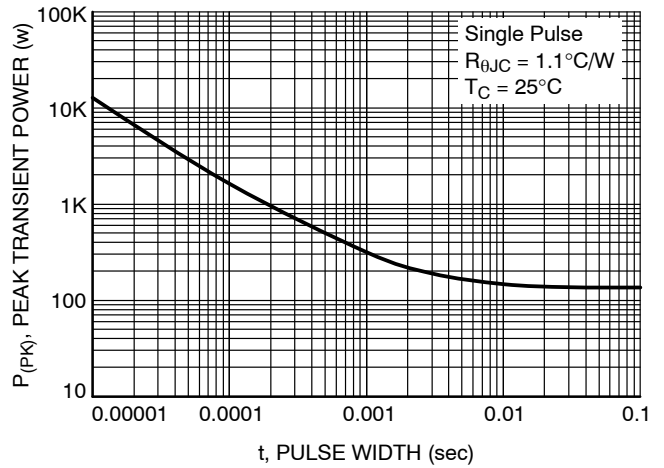


Figure 12. Single Pulse Maximum Power Dissipation

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TYPICAL CHARACTERISTICS

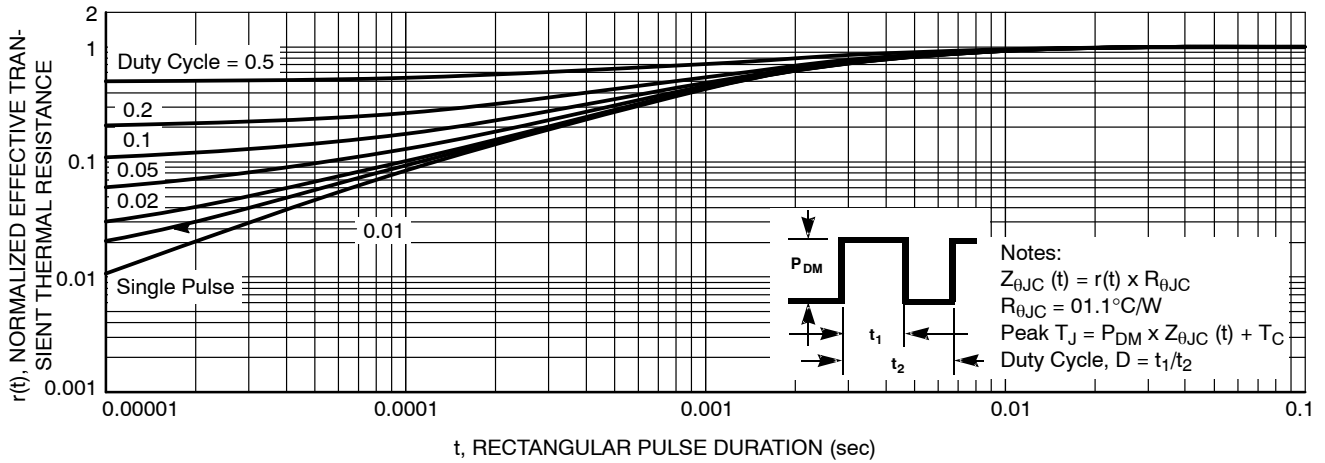


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

DEVICE ORDERING INFORMATION

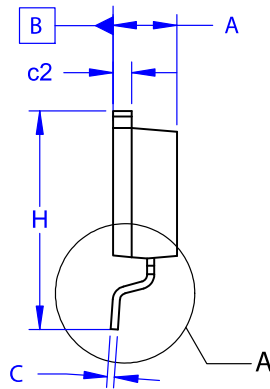
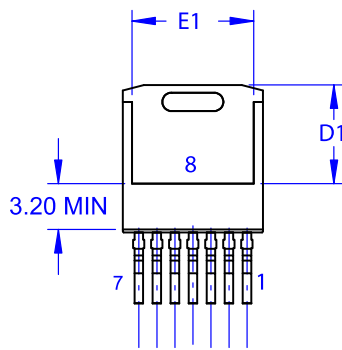
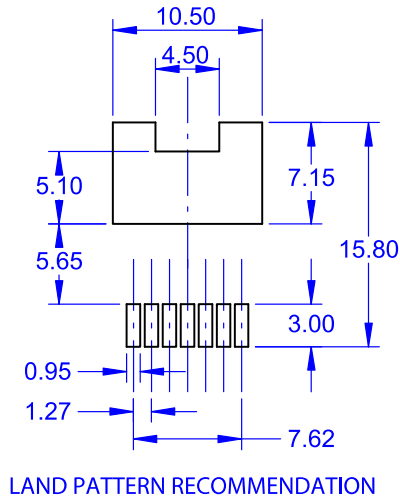
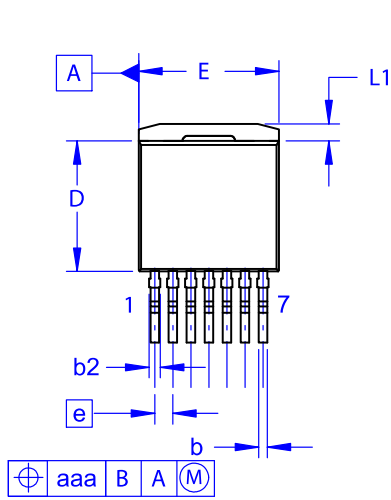
Device	Package	Shipping†
NVBG160N120SC1	D2PAK-7L	800 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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PACKAGE DIMENSIONS

D²PAK7 (TO-263-7L HV)
CASE 418BJ
ISSUE B



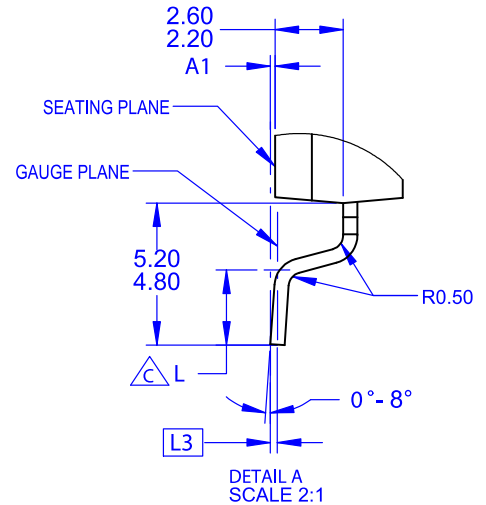
NOTES:

- A. PACKAGE CONFORMS TO JEDEC TO-263 VARIATION CB EXCEPT WHERE NOTED.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.


\triangle OUT OF JEDEC STANDARD VALUE.
D. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.

- E. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.30	4.50	4.70
A1	0.00	0.10	0.20
b2	0.60	0.70	0.80
b	0.51	0.60	0.70
c	0.40	0.50	0.60
c2	1.20	1.30	1.40
D	9.00	9.20	9.40
D1	6.15	6.80	7.15
E	9.70	9.90	10.20
E1	7.15	7.65	8.15
e	~	1.27	~
H	15.10	15.40	15.70
L	2.44	2.64	2.84
L1	1.00	1.20	1.40
L3	~	0.25	~
aaa	~	~	0.25



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